DEC 2 8 2000 Attorney Docket No. Serial No. 09/532,915 SEL 170 <u>Applicant</u> LIST OF PUBLICATION Masahiko HAYAKAWA et al CITED BY APPLICANT Filing Date Group March 22, 2000 2811 U.S. PATENT DOCUMENTS SUB-FILING *EXAMINER DOCUMENT INITIAL NUMBER DATE NAME CLASS CLASS DATE FOREIGN PATENT DOCUMENTS DOCUMENT SUB-FILING CLASS CLASS DATE DATE NAME NUMBER 05/22/98 10/24/96 JP 10-135469 Semiconductor Energy Laboratory Co., Ltd. OTHER PUBLICATIONS (Including Author, Title, Date, Pertinent Pages) English abstract re Japanese patent application no. 10-135469, published May 22, 1998. DATE CONSIDERED:

EXAMINER:

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LIST OF PUBLICATIONS CITED BY APPLICANT	Attorney Docket No. SEL 170	<u>Serial No.</u> 09/532,915
	<u>Applicant</u> Masahiko HAYAKAWA et al	
	<u>Filing Date</u> March 22, 2000	Group 2811

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